NST489AMT1G, NSVT489AMT1G

High Current Surface Mount NPN Silicon Low V_{CE(sat)} Switching Transistor for Load Management in Portable Applications

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	30	V
Collector-Base Voltage	V _{CBO}	50	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current – Continuous	I _C	2.0	Α
Collector Current – Peak	I _{CM}	3.0	Α

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D (Note 1)	535 4.3	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 1)	234	°C/W
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D (Note 2)	1.180 9.4	W mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 2)	106	°C/W
Thermal Resistance, Junction-to-Lead #1	R _{θJL} (Note 1) R _{θJL} (Note 2)	110 50	°C/W °C/W
Total Device Dissipation (Single Pulse < 10 s)	P _{Dsingle} (Notes 2 and 3)	1.75	W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-4 with 1 oz and 3.9 mm² of copper area.
- 2. FR-4 with 1 oz and 645 mm² of copper area.
- 3. Refer to Figure 8.



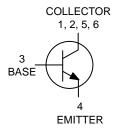
ON Semiconductor®

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30 VOLTS, 3.0 AMPS NPN TRANSISTOR



TSOP-6 CASE 318G STYLE 6



DEVICE MARKING



N2 = Specific Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
NST489AMT1G	TSOP-6 (Pb-Free)	3,000 / Tape & Reel
NSVT489AMT1G	TSOP-6 (Pb-Free)	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage (I _C = 10 mA	$I_{A}, I_{B} = 0$	V _{(BR)CEO}	30	_	_	V
Collector-Base Breakdown Voltage (I _C = 0.1 mA,	I _E = 0)	V _{(BR)CBO}	50	-	-	V
Emitter – Base Breakdown Voltage (I _E = 0.1 mA, I _C	; = 0)	V _{(BR)EBO}	5.0	_	-	V
Collector Cutoff Current (V _{CB} = 30 V, I _E = 0)	I _{CBO}	-	_	0.1	μΑ	
Collector–Emitter Cutoff Current (V _{CES} = 30 V)		I _{CES}	-	_	0.1	μΑ
Emitter Cutoff Current (V _{EB} = 4.0 V)		I _{EBO}	-	_	0.1	μΑ
ON CHARACTERISTICS						
DC Current Gain (Note 4)	$ \begin{array}{l} (I_{C} = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}) \\ (I_{C} = 0.5 \text{ A}, V_{CE} = 5.0 \text{ V}) \\ (I_{C} = 1.0 \text{ A}, V_{CE} = 5.0 \text{ V}) \end{array} $	h _{FE}	300 300 200	500 -	900 -	
Collector - Emitter Saturation Voltage (Note 4)	$(I_C = 1.0 \text{ A}, I_B = 100 \text{ mA})$ $(I_C = 0.5 \text{ A}, I_B = 50 \text{ mA})$ $(I_C = 0.1 \text{ A}, I_B = 1.0 \text{ mA})$	V _{CE(sat)}	- - -	0.10 0.06 0.05	0.200 0.125 0.075	V
Base – Emitter Saturation Voltage (Note 4) (I _C = 1.0 A, I _B = 0.1 A)		V _{BE(sat)}	-	-	1.1	V
Base – Emitter Turn–on Voltage (Note 4) (I _C = 1.0 A, V _{CE} = 2.0 V)		V _{BE(on)}	-	-	1.1	V
Cutoff Frequency (I _C = 100 mA, V _{CE} = 5.0 V, f = 100 MHz		f _T	200	300	-	MHz
Output Capacitance (f = 1.0 MHz)		C _{obo}	-	_	15	pF

^{4.} Pulsed Condition: Pulse Width \leq 300 μ sec, Duty Cycle \leq 2%.

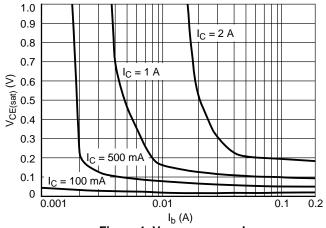


Figure 1. V_{CE (sat)} versus I_b

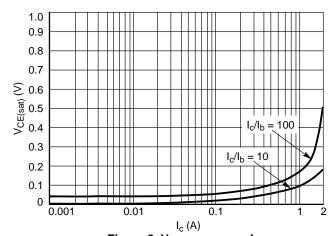


Figure 2. V_{CE (sat)} versus I_c

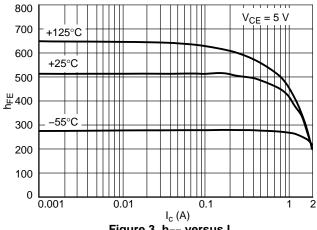


Figure 3. h_{FE} versus I_c

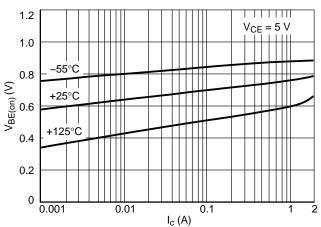
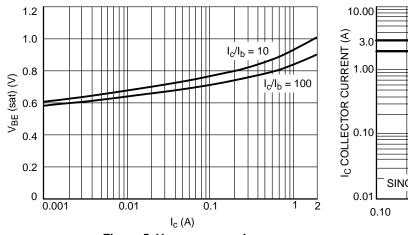


Figure 4. $V_{\rm BE(on)}$ versus $I_{\rm c}$

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10.00

3.0

1.00

1 ms
10 ms
100 ms
1 s
100 ms
1 s
100 ms
100 ms
1 s

Figure 5. $V_{BE(sat)}$ versus I_c

Figure 6. Safe Operating Area

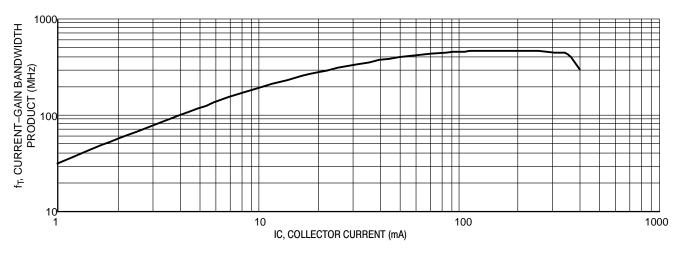


Figure 7. f_T (MHZ) versus I_C (mA) V_{CE} = 5.0 V

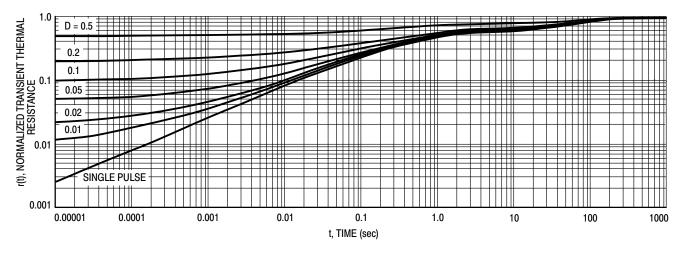


Figure 8. Normalized Thermal Response





NOTE 5

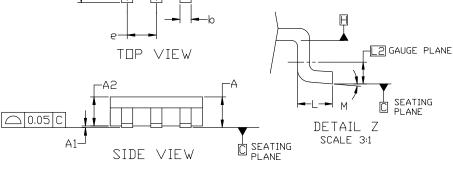
TSOP-6 3.00x1.50x0.90, 0.95P **CASE 318G ISSUE W**

DATE 26 FEB 2024

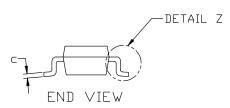


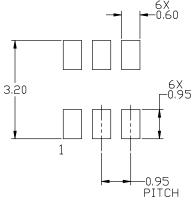
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM
 LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.

 5. PIN 1 INDICATOR MUST BE LOCATED IN THE INDICATED ZONE



N	1ILLIM	IETERS	2
DIM	MIN	NDM	MAX
Α	0.90	1.00	1.10
A1	0.01	0.06	0.10
A2	0.80	0.90	1.00
b	0.25	0.38	0.50
C	0.10	0.18	0.26
D	2.90	3.00	3,10
E	2.50	2.75	3.00
E1	1.30	1.50	1.70
е	0.85	0.95	1.05
L	0.20	0.40	0.60
L2	0.25 BSC		
М	0°		10°





RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference manual, SDLDERRM/D.

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ISSUE W

DATE 26 FEB 2024

GENERIC MARKING DIAGRAM*



XXX M= **STANDARD**

XXX = Specific Device Code

XXX = Specific Device Code

=Assembly Location

= Date Code

= Year

= Pb-Free Package

W = Work Week

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 2: PIN 1. EMITTER 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. BASE 2 6. COLLECTOR 2	STYLE 3: PIN 1. ENABLE 2. N/C 3. R BOOST 4. Vz 5. V in 6. V out	STYLE 4: PIN 1. N/C 2. V in 3. NOT USED 4. GROUND 5. ENABLE 6. LOAD	STYLE 5: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 6: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR
STYLE 7: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. N/C 5. COLLECTOR 6. EMITTER	STYLE 8: PIN 1. Vbus 2. D(in) 3. D(in)+ 4. D(out)+ 5. D(out) 6. GND	STYLE 9: PIN 1. LOW VOLTAGE GATE 2. DRAIN 3. SOURCE 4. DRAIN 5. DRAIN 6. HIGH VOLTAGE GATE	2. GND ' 3. D(OUT)- 4. D(IN)- 5. VBUS	STYLE 11: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1/GATE 2	STYLE 12: PIN 1. I/O 2. GROUND 3. I/O 4. I/O 5. VCC 6. I/O
STYLE 13: PIN 1. GATE 1 2. SOURCE 2 3. GATE 2 4. DRAIN 2 5. SOURCE 1 6. DRAIN 1	STYLE 14: PIN 1. ANODE 2. SOURCE 3. GATE 4. CATHODE/DRAIN 5. CATHODE/DRAIN 6. CATHODE/DRAIN		/LE 16: N 1. ANODE/CATHODE 2. BASE 3. EMITTER 4. COLLECTOR 5. ANODE 6. CATHODE	STYLE 17: PIN 1. EMITTER 2. BASE 3. ANODE/CATHODE 4. ANODE 5. CATHODE 6. COLLECTOR	

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